Toshiba Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1030F

2-IN-1 Low-Side Switch for Motor, Solenoid and Lamp Drive

The TPD1030F is a 2-IN-1 low-side switch.

The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC is equipped with intelligent self-protection functions.

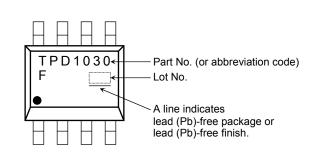
Features

- Two built-in power IC chips with a new structure combining a control block and a vertical power MOSFET (L²-π-MOS) on each chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in protection circuits against overvoltage (active clamp),
 overtemperature (thermal shutdown), and overcurrent (current limiter).
- Low Drain-Source ON-resistance: RDS (ON) = 0.6Ω (max) (@VIN = 5 V, ID = 0.5 A, Tch = 25° C)
- Low Leakage Current: $I_{DSS} = 10 \mu A \text{ (max) (@V_{IN} = 0 V, V_{DS} = 30 V, T_{ch} = 25 ^{\circ}\text{C})}$
- Low Input Current: $I_{IN} = 300 \mu A \text{ (max) } (@V_{IN} = 5 \text{ V}, T_{ch} = 25 ^{\circ}\text{C})$
- 8-pin SOP package with embossed-tape packing.

Pin Assignment (top view)

SOURCE1 1 8 DRAIN1 IN1 2 7 DRAIN1 SOURCE2 3 6 DRAIN2 IN2 4 5 DRAIN2

Marking



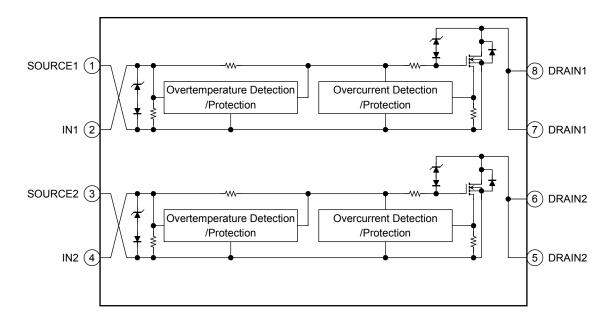
Weight: 0.08 g (typ.)

SOP8-P-1.27A

Note1: Due to its MOS structure, this product is sensitive to static electricity.

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Block Diagram

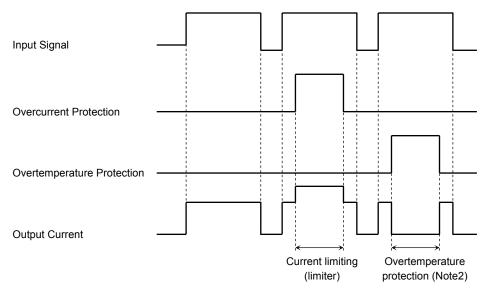


Pin Description

Pin No.	Symbol	Pin Description				
1	SOURCE1	Source pin 1				
2	IN1	Input pin 1				
		This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.				
3	SOURCE2	Source pin 2				
4	IN2	Input pin 2				
		This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.				
F 6	DRAIN2	Drain pin 2				
5, 6		Drain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.				
7 0	DRAIN1	Drain pin 1				
7, 8		Drain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.				

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Timing Chart



Note2: The overheating detector circuits feature hysteresis. After overheating is detected, normal operation is restored only when the channel temperature falls by the hysteresis amount (5°C typ.) in relation to the overheating detection temperature.

Truth Table

IN	V _{OUT}	Mode		
L	Н	Normal		
Н	L	Noma		
L	Н	Overcurrent		
Н	Н	Overcurrent		
L	Н	Overtemperature		
Н	Н	Overtemperature		

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DS} (DC)	40	V
Drain current	I _D	Internally Limited	Α
Input voltage	V _{IN}	-0.3 to 7	V
Power dissipation (t = 10 s)	P _D	2.0 (Note 3)	W
Single pulse active clamp capability (Note 4)	E _{AS}	10	mJ
Active clamp current	I _{AR}	1	Α
Repetitive active clamp capability (Note 5)	E _{AR}	0.2	mJ
Operating temperature	T _{opr}	T _{opr} –40 to 110	
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient (t = 10 s) (No.	ote3)	R _{th (ch-a)}	62.5	°C/W

Note 3: Drive operation: Mounted on glass epoxy board [25.4mm \times 25.4mm \times 0.8mm] (with the two devices operating)

Note 4: Active clamp capability (single pulse) test condition $V_{DD}=25~V,~Starting~T_{Ch}=25^{\circ}C,~L=10~mH,~I_{AR}=1~A,~R_{G}=25~\Omega$

Note 5: Repetitive rating, pulse width limited by maximum channel temperature.

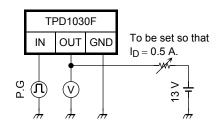
Electrical Characteristics

Characteristics	Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Drain-source clamp voltage	V _{(CL) DSS}	_	T _{ch} =-40~110°C	V _{IN} = 0 V, I _D =1mA	40	_	60	٧
Input throubold voltage	V _{th}	_	T _{ch} =25°C	V _{DS} = 13 V, I _D =10mA	1.0	_	2.8	V
Input threshold voltage			T _{ch} =-40~110°C		0.9	_	3.0	
Protective circuit operation	.,	_	T _{ch} =25°C	_	3	_	7	V
input voltage range	V _{IN (opr)}		T _{ch} =-40~110°C	_	3.5	_	7	V
Drain cut-off current	IDSS	_	T _{ch} =25°C	V _{IN} = 0 V, V _{DS} =30V	_	_	10	μА
			T _{ch} =-40~110°C		_	_	100	
	I _{IN (1)}	_	T _{ch} =25°C	V _{IN} = 5 V, at normal operation	_	_	300	
Input current	I _{IN (2)}	_	T _{ch} =-40~110°C	V _{IN} = 5 V, when overcurrent protective circuit is actuated	_	_	350	μА
Drain source on registance	R _{DS} (ON)	_	T _{ch} =25°C	$V_{IN} = 5 V$,	_	0.44	0.6	Ω
Drain-source on resistance			T _{ch} =-40~110°C	I _D = 0.5 A	_	_	0.9	
Overtemperature protection	T _S	_	_	V _{IN} = 5 V	150	160	_	°C
Oversurrent pretection	IS	_	T _{ch} =25°C	V _{IN} = 5 V	1	1.8	_	A
Overcurrent protection			T _{ch} =-40~110°C		0.7	_	_	
	t _{ON}		T _{ch} =25°C	V _{DD} = 13 V, V _{IN} = 0V/5 V, I _D = 0.5 A	_	_	30	μs
Consideration on Alice of			T _{ch} =-40~110°C			_	60	
Switching time	toff	1	T _{ch} =25°C			_	60	
			T _{ch} =-40~110°C	1	_	_	90	
Source-drain diode forward voltage	V _{DSF}	_	T _{ch} =25°C	I _F = 1 A, V _{IN} = 0 V	_	_	1.7	V

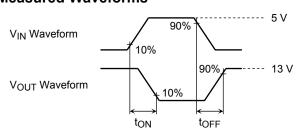
Test Circuit 1

Switching time measuring circuit

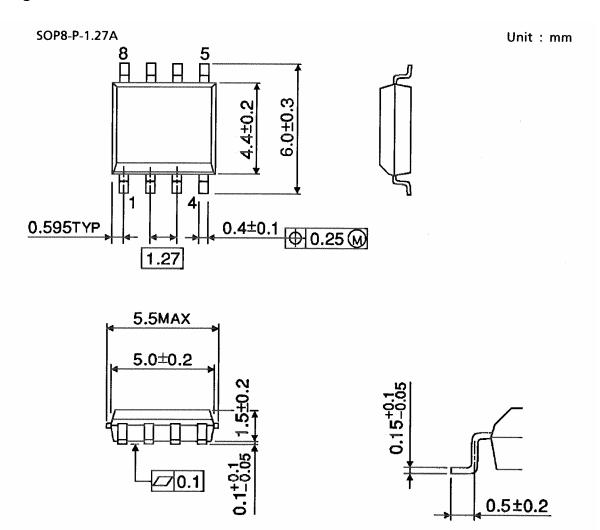
Test Circuit



Measured Waveforms



Package Dimensions



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Weight: 0.08 g (typ.)

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